
2SC5079

Silicon NPN Epitaxial

HITACHI

ADE-208-222
1st. Edition

Application

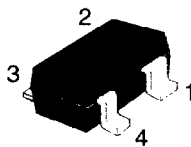
VHF / UHF wide band amplifier

Features

- High gain bandwidth product
 $f_T = 12 \text{ GHz Typ}$
- High gain, low noise figure
 $PG = 17 \text{ dB Typ}$, $NF = 1.6 \text{ dB Typ}$ at $f = 900 \text{ MHz}$

Outline

CMPAK-4



1. Collector
2. Emitter
3. Base
4. Emitter

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Rated	Unit
Collector to base voltage	V_{CBO}	15	V
Collector to emitter voltage	V_{CEO}	8	V
Emitter to base voltage	V_{EBO}	1.5	V
Collector current	I_C	20	mA
Collector power dissipation	P_C	100	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector cutoff current	I_{CBO}	—	—	10	μ A	$V_{CB} = 15$ V, $I_E = 0$
	I_{CEO}	—	—	1	mA	$V_{CE} = 8$ V, $R_{BE} = \infty$
Emitter cutoff current	I_{EBO}	—	—	10	μ A	$V_{EB} = 1.5$ V, $I_C = 0$
DC current transfer ratio	h_{FE}	50	120	160		$V_{CE} = 5$ V, $I_C = 10$ mA
Collector output capacitance	C_{ob}	—	0.3	0.8	pF	$V_{CB} = 5$ V, $I_E = 0$, $f = 1$ MHz
Gain bandwidth product	f_T	9	12	—	GHz	$V_{CE} = 5$ V, $I_C = 5$ mA
Power gain	PG	14	17	20	dB	$V_{CE} = 5$ V, $I_C = 10$ mA, $f = 900$ MHz
Noise figure	NF	—	1.6	2.5	dB	$V_{CE} = 5$ V, $I_C = 5$ mA, $f = 900$ MHz

Note: Marking is "ZC--".

Attention: This device is very sensitive to electro static discharge.

It is recommended to adopt appropriate cautions when handling this transistor.

See characteristic curves of 2SC5078.

